# MBR1635, MBR1645, MBRB1645, NRVBB1645

# Switch-mode Power Rectifiers

16 A, 35 and 45 V

These state-of-the-art devices use the Schottky Barrier principle with a platinum barrier metal.

#### **Features**

- Guard-ring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- NRVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

### **Mechanical Characteristics:**

- Case: Epoxy, Molded
- Weight: 1.9 Grams for TO-220
  - 1.7 Grams for D<sup>2</sup>PAK
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage MBR1635 MBR1645 MBRB1645	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	35 45 45	V
Average Rectified Forward Current Delay (Rated V <sub>R</sub> , T <sub>C</sub> = 163°C) Total Device	I <sub>F(AV)</sub>	16	Α
Peak Repetitive Forward Current, Per Leg (Rated V <sub>R</sub> , Square Wave, 20 kHz, T <sub>C</sub> = 157°C) Total Device	I <sub>FRM</sub>	32	Α
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I <sub>FSM</sub>	150	Α
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I <sub>RRM</sub>	1.0	Α
Storage Temperature Range	T <sub>stg</sub>	-65 to +175	°C
Operating Junction Temperature (Note 1)	$T_J$	-65 to +175	°C
Voltage Rate of Change (Rated V <sub>R</sub> )	dv/dt	10,000	V/μs

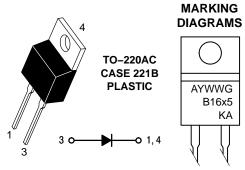
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient:  $dP_D/dT_J < 1/R_{\theta,JA}$ .



### ON Semiconductor®

### http://onsemi.com



A = Assembly Location

Y = Year

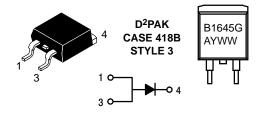
WW = Work Week

B16x5 = Device Code

x = 3 or 4

KA = Diode Polarity

G = Pb-Free Package



B1645 = Device Code A = Assembly Location

Y = Year
WW = Work Week
G = Pb-Free Package

### **ORDERING INFORMATION**

Device	Package	Shipping
MBR1635G	TO-220 (Pb-Free)	50 Units / Rail
MBR1645G	TO-220 (Pb-Free)	50 Units / Rail
MBRB1645T4G	D <sup>2</sup> PAK (Pb-Free)	800 Units / Rail
NRVBB1645T4G	D <sup>2</sup> PAK (Pb-Free)	800 Units / Rail

## MBR1635, MBR1645, MBRB1645, NRVBB1645

### THERMAL CHARACTERISTICS

Characteristic		Symbol	Value	Unit
Maximum Thermal Resistance,	Junction-to-Case	$R_{ heta JC}$	1.5	°C/W

### **ELECTRICAL CHARACTERISTICS**

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 2) ( $i_F = 16 \text{ Amps}, T_C = 125^{\circ}\text{C}$ ) ( $i_F = 16 \text{ Amps}, T_C = 25^{\circ}\text{C}$ )	VF	0.57 0.63	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_C = 125^{\circ}C$ ) (Rated dc Voltage, $T_C = 25^{\circ}C$ )	i <sub>R</sub>	40 0.2	mA

<sup>2.</sup> Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

### MBR1635, MBR1645, MBRB1645, NRVBB1645

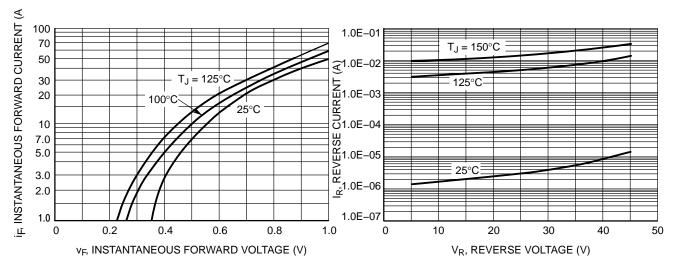


Figure 1. Typical Forward Voltage

**Figure 2. Typical Reverse Current** 

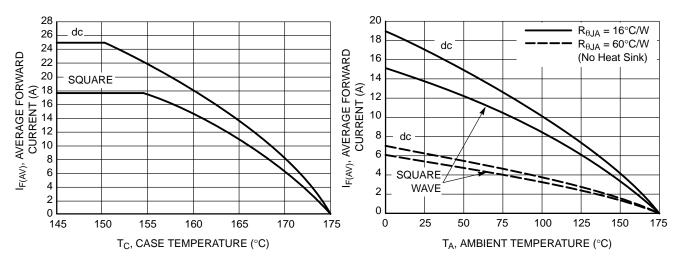


Figure 3. Current Derating, Case, Per Leg

Figure 4. Current Derating, Ambient

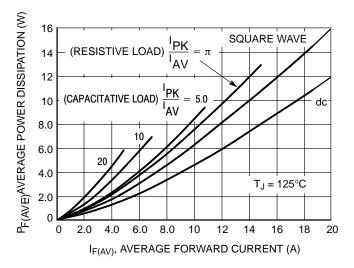


Figure 5. Forward Power Dissipation

# **MECHANICAL CASE OUTLINE**

**PACKAGE DIMENSIONS** 



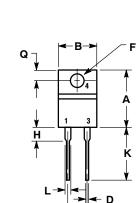


TO-220, 2-LEAD CASE 221B-04 ISSUE F

**DATE 12 APR 2013** 

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

_				
	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.595	0.620	15.11	15.75
В	0.380	0.405	9.65	10.29
С	0.160	0.190	4.06	4.82
D	0.025	0.039	0.64	1.00
F	0.142	0.161	3.61	4.09
G	0.190	0.210	4.83	5.33
Н	0.110	0.130	2.79	3.30
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.14	1.52
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.14	1.39
T	0.235	0.255	5.97	6.48
U	0.000	0.050	0.000	1.27



STYLE 1: PIN 1. CATHODE 2. N/A 3. ANODE

PIN 1. ANODE 2. N/A 3. CATHODE 4. ANODE

DOCUMENT NUMBER:	98ASB42149B	Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	TO-220, 2-LEAD		PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

## **MECHANICAL CASE OUTLINE**

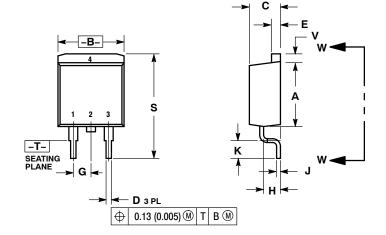




D<sup>2</sup>PAK 3 CASE 418B-04 **ISSUE L** 

**DATE 17 FEB 2015** 

### SCALE 1:1



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
   CONTROLLING DIMENSION: INCH.
- 3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

	INCHES		INCHES MILLIMETER	
DIM	MIN	MAX	MIN	MAX
Α	0.340	0.380	8.64	9.65
В	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
Е	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
Н	0.080	0.110	2.03	2.79
7	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
М	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
Р	0.079 REF		2.00 REF	
R	0.039 REF		0.99	REF
S	0.575	0.625	14.60	15.88
٧	0.045	0.055	1.14	1.40



STYLE 1: PIN 1. BASE 2. COLLECTOR
3. EMITTER
4. COLLECTOR STYLE 2: PIN 1. GATE 2. DRAIN

3. SOURCE 4. DRAIN

STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE

STYLE 4:

PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 5: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. ANODE

STYLE 6: PIN 1. NO CONNECT
2. CATHODE
3. ANODE
4. CATHODE

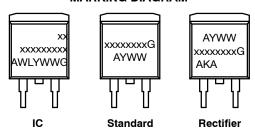
### **MARKING INFORMATION AND FOOTPRINT ON PAGE 2**

DOCUMENT NUMBER:	98ASB42761B	Electronic versions are uncontrolled except when accessed directly from the Document Repo Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	D <sup>2</sup> PAK 3		PAGE 1 OF 2

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

**DATE 17 FEB 2015** 

# GENERIC MARKING DIAGRAM\*



xx = Specific Device Code A = Assembly Location

 WL
 = Wafer Lot

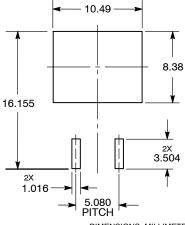
 Y
 = Year

 WW
 = Work Week

 G
 = Pb-Free Package

 AKA
 = Polarity Indicator

### **SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

DOCUMENT NUMBER:	98ASB42761B	Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	D <sup>2</sup> PAK 3		PAGE 2 OF 2

ON Semiconductor and at a trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot " ■", may or may not be present.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer pu

#### **PUBLICATION ORDERING INFORMATION**

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

## onsemi:

MBR1645 MBRB1645T4G MBR1635 MBR1635G MBR1645G NRVBB1645T4G